

Form PTO-1449 (Rev. 8-83)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTORNEY DOCKET NO. 12734US02	SERIAL NO. 10/684,910
INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)		APPLICANT: Donald J. Sawdai et al.	
		FILING DATE	GROUP ART UNIT: 2818

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TH	A	3,746,950	07-17-73	Kano et al.			
TH	B	4,859,616	08-22-89	Losehand et al.			
TH	C	5,055,890	10-08-91	Dawson et al.			
	D						
	E						
	F						
	G						
	H						

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

TH	AA	Physics of Semiconductor Devices, 2 <sup>nd</sup> Edition, by S.M. Sze; John Wiley & Sons, N.Y., 1981, pages 282-311.
I	BB	Controlled Formation of High Schottky Barriers on InP and Related Materials, by Hideki Hasegawa; May 11-15, 1998 IEEE.
I	CC	Nearly Ideal Schottky Contacts of n-InP by Z.Q. Shi and W.A. Anderson, State University of New York at Buffalo, IPRM 1991.
TH	DD	Schottky contacts to InP, InGaAs and InAlAs, by S. Wilks, L. Jenkins, J. Morris, S. Clark and R.H. Williams, University of Wales College of Cardiff, IPRM 1991.
EXAMINER	DATE CONSIDERED	
TU - TU +10	Feb. 2004	

\*EXAMINER: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.